

DAFTAR PUSTAKA

- Bart J. van Zeghbroeck. (1998). *Carrier Transport*, [online]. Tersedia: <file:///E:/2.8carriertransport.htm>
- B. Podor // *Phys. Status solidi* 16, p. k167 (1966).
- C. Erginsoy // *Phys. Rev.* 79, p. 1013 (1950).
- D.A Anderson and N. Apsley. "*Semiconductor Science and Technology 1*", June 9 (1986).
- D.C Look, "*Electrical characterization of GaAs material and devices*", Wiley, New York, 1989.
- D.C Look, J.R. Sizelove. "*Dislocation scattering in GaN*", *Phys. Rev. Lett.* 82, No. 6, 1999
- E. F. Schubert. "*High Electron Mobility Transistor*", Rensselaer Polytechnic Institute (2003).
- H. Arabshahi. "*Calculation Of Electron Hall Mobility in GaSb, GaAs and GaN Using an Iterative Method*", Physics Department, Ferdowsi University of Mashhad, Mashhad, Iran (2008).
- Janardan Kundu, C.K. Sarkar, P.S. Mallick. "*Calculation Of Electron Mobility and Effect Of Dislocation Scattering in GaN*", National Institute Of Science and Technology, Palur Hills, Berhampur, India (2007).
- NSM-archive. *GaN-Gallium Nitride*, [online]. Tersedia: <http://www.ioffe.ru/SVA/NSM/Semicond/GaN/>
- Prof. Dr. Hadis Morkoc. "*Handbook of Nitride Semiconductors and Devices*", Wiley-VCH (2008).

Prof. Dr. Hadis Morkoc. "*Handbook of Nitride Semiconductors and Devices*", Wiley-VCH (2008).

S Aydogu, M. Akarsu, O. Ozbas, "*Numerical Calculation Of The Electron Mobility Of GaN Semiconductor Compound*", Osmangazi University, Department Of Physics, Eskisehir, Turkey, (2004).

S.C. Jain, M. Willander, J. Narayan and R. Van Overstraeten. "*III-nitrides: growth, characterization and properties*", J. Appl. Phys. 87, No. 3, p. 965-1006 (2000).

Sibel Gokden. "*Electron Transport Mechanism in GaN/AlGaN HEMT Structures*", Bahkesir University, Department of Physics, Bahkesir, Turkey.

S. Nakamura, S.J. Pearton and G. Fasal. "*The blue LASER diodes*", Springer, Berlin, 2000.

Subhabrata Dhar and Subhasis Ghosh // J. Appl. Phys. 86 (5), 1st Sept. (1999).